

250mA Low-Dropout Regulator for C2000™

Check for Samples: TPS73219

FEATURES

- Optimal Output Voltage for Core Rail of C2000
- Good Line/Load Transient Response for MCUs
- 250mA LDO Voltage Regulator with Enable
- Very Low Dropout Voltage: 40mV (typ) at 250mA
- Reverse Current Protection
- Stable with or without Output Capacitor
- 1% Overall Accuracy (Line, Load, and Temperature)
- Available in a 5-Pin SOT23 Package

APPLICATIONS

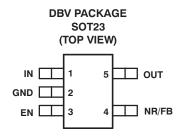
C2000 Core Power Rail Supply

DESCRIPTION

The TPS73219 family is a low-dropout (LDO) voltage regulator that offers very good line and load transient response even without the use of an output capacitor. The TPS73219 is ideal for driving the C2000 MCUs fron Texas Instruments. The device offers very low dropout voltage, thereby reducing power loss.

In combination with a voltage supervisor such as the TPS3808G19 or TPS3808G01, the TPS73219 can deliver tight V_{CORE} voltages and generate accurate power-good signals that meet or exceed power requirements for the C2000.

The TPS73219 is available in a 5-pin SOT23 package.



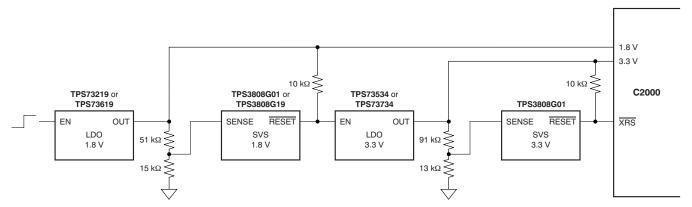


Figure 1. Typical Application

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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All other trademarks are the property of their respective owners.





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION(1)

PRODUCT	V _{OUT} ⁽²⁾
TPS732 xx <i>yy yz</i>	XX is nominal output voltage (for example, 25 = 2.5V, 01 = Adjustable ⁽³⁾). YYY is package designator. Z is package quantity.

- (1) For the most current specification and package information, refer to the Package Option Addendum located at the end of this datasheet or see the TI website at www.ti.com.
- (2) Most output voltages of 1.25V and 1.3V to 5.0V in 100mV increments are available through the use of innovative factory EEPROM programming; minimum order quantities may apply. Contact factory for details and availability.
- (3) For fixed 1.20V operation, tie FB to OUT.

ABSOLUTE MAXIMUM RATINGS

Over operating junction temperature range unless otherwise noted. (1)

PARAMETER	TPS73219	UNIT			
V _{IN} range	-0.3 to 6.0	V			
V _{EN} range	-0.3 to 6.0	V			
V _{OUT} range	-0.3 to 5.5	V			
V _{NR} , V _{FB} range	-0.3 to 6.0	V			
Peak output current	Internally limited				
Output short-circuit duration	Indefinite				
Continuous total power dissipation	See Thermal Information Table				
Junction temperature range, T _J	-55 to +150	°C			
Storage temperature range	-65 to +150	°C			
ESD rating, HBM	2	kV			
ESD rating, CDM	500	V			

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under the Electrical Characteristics is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.



THERMAL INFORMATION

		TPS73219 ⁽³⁾	
	THERMAL METRIC ⁽¹⁾⁽²⁾	DBV	UNITS
		5 PINS	
θ_{JA}	Junction-to-ambient thermal resistance (4)	180	
θ_{JCtop}	Junction-to-case (top) thermal resistance ⁽⁵⁾	64	
θ_{JB}	Junction-to-board thermal resistance (6)	35	0000
Ψлт	Junction-to-top characterization parameter ⁽⁷⁾	N/A	°C/W
ΨЈВ	Junction-to-board characterization parameter ⁽⁸⁾	N/A	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance (9)	N/A	

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953A.
- (2) For thermal estimates of this device based on PCB copper area, see the TI PCB Thermal Calculator.
- 3) Thermal data for the DRB, DCQ, and DRV packages are derived by thermal simulations based on JEDEC-standard methodology as specified in the JESD51 series. The following assumptions are used in the simulations:
 - (a) There is no exposed pad with the DBV package.
 - (b) The top and bottom copper layers are assumed to have a 20% thermal conductivity of copper representing a 20% copper coverage.
 - (c) These data were generated with only a single device at the center of a JEDEC high-K (2s2p) board with 3in × 3in copper area. To understand the effects of the copper area on thermal performance, see the *Power Dissipation* section of this data sheet.
- (4) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (5) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the top of the package. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (6) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (7) The junction-to-top characterization parameter, ψ_{JT} , estimates the junction temperature of a device in a real system and is extracted from the simulation data to obtain θ_{JA} using a procedure described in JESD51-2a (sections 6 and 7).
- (8) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data to obtain θ_{JA} using a procedure described in JESD51-2a (sections 6 and 7).
- (9) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.



ELECTRICAL CHARACTERISTICS

Over operating temperature range (T $_J$ = -40°C to +125°C), V $_{IN}$ = 2.4V, I $_{OUT}$ = 10mA, V $_{EN}$ = 1.7V, and C $_{OUT}$ = 0.1 μ F, unless otherwise noted. Typical values are at T $_J$ = 25°C.

	PARAMETER	PARAMETER TEST CONDITIONS				TYP	MAX	UNIT		
V _{IN}	Input voltage range				2.05		5.5	V		
		Accuracy $ \begin{array}{c c} Nominal & T_J = +25^{\circ}C \\ \hline V_{IN}, \ I_{OUT}, \ and \ T & V_{OUT} + 0.5V \le \\ 10 \ mA \le I_{OUT} \end{array} $			-0.5		+0.5			
V _{OUT}	Accuracy			≤ V _{IN} ≤ 5.5V; ≤ 250mA	-1.0	±0.5	+1.0	%		
$\Delta V_{OUT}\%/\Delta V_{IN}$	Line regulation		V _{OUT(nom)} + 0	.5V ≤ V _{IN} ≤ 5.5V		0.01		%/V		
۸۱/ ۵//۸۱	Load regulation		1mA ≤ I _{OUT} ≤	250mA		0.002		%/mA		
$\Delta V_{OUT} \% / \Delta I_{OUT}$	Load regulation		10mA ≤ I _{OUT} :	≤ 250mA		0.0005		70/IIIA		
V_{DO}	Dropout voltage (V _{IN} = V _{OUT} (nom) –	0.1V)	I _{OUT} = 250mA	1		40	150	mV		
Z _O (DO)	Output impedance in	n dropout	1.7 V ≤ V _{IN} ≤	V _{OUT} + V _{DO}		0.25		Ω		
I _{CL}	Output current limit		V _{OUT} = 0.9 ×	$V_{OUT(nom)}$	250	425	600	mA		
I _{SC}	Short-circuit current		$V_{OUT} = 0V$			300		mA		
I _{REV}	Reverse leakage cu	rrent ⁽¹⁾ (–I _{IN})	$V_{EN} \le 0.5 V, 0$	$V \le V_{IN} \le V_{OUT}$		0.1	10	μΑ		
loup	GND pin current		$I_{OUT} = 10mA$	(I_Q)		400	550	μA		
I _{GND}	GND pin current		$I_{OUT} = 250 \text{m/s}$	1		650	950) μΑ		
I _{SHDN}	Shutdown current (Id	GND)	V _{EN} ≤ 0.5V, V -40°C ≤ T _J ≤	′ _{OUT} ≤ V _{IN} ≤ 5.5, +100°C		0.02	1	μΑ		
PSRR	Power-supply rejecti	on ratio	f = 100Hz, I _{OUT} = 250 mA			58		dB		
PSKK	(ripple rejection)		f = 10kHz, I _{Ol}	_{JT} = 250 mA		37		uБ		
V	Output noise voltage	out noise voltage $C_{OUT} = 10\mu F$, No C_{NR}		2	7 × V _{OUT}		\/			
V_N	BW = 10Hz - 100kH	łz	$C_{OUT} = 10\mu F$,	$C_{NR} = 0.01 \mu F$	8.8	5 × V _{OUT}		μV_{RMS}		
t _{STR}	Startup time		$V_{OUT} = 3V, R$ $C_{OUT} = 1 \mu F,$	$_{L} = 30Ω$ $C_{NR} = 0.01 \mu F$		600		μs		
V _{EN} (HI)	EN pin high (enable	d)			1.7		V_{IN}	V		
V _{EN} (LO)	EN pin low (shutdow	vn)			0		0.5	V		
I _{EN} (HI)	EN pin current (enal	oled)	$V_{EN} = 5.5V$			0.02	0.1	μΑ		
T	Thormal chutdows t	omporaturo	Shutdown Temp increasing			+160		°C		
T _{SD}	Thermal shutdown temperature		Reset Temp decreasing +140					°C		
T_J	Operating junction to	emperature			-40		+125	°C		

⁽¹⁾ Fixed-voltage versions only; refer to *Applications* section for more information.

FUNCTIONAL BLOCK DIAGRAM

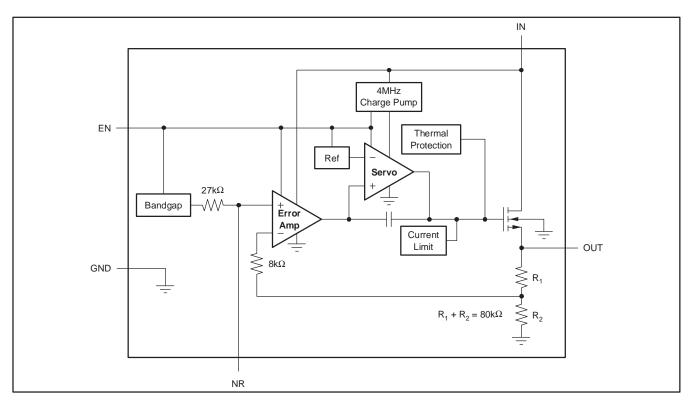
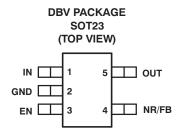


Figure 2. Fixed Voltage Version

PIN CONFIGURATION



PIN DESCRIPTIONS

NAME	SOT23 (DBV) PIN NO.	DESCRIPTION
IN	1	Input supply
GND	2	Ground
EN	3	Driving the enable pin (EN) high turns on the regulator. Driving this pin low puts the regulator into shutdown mode. Refer to the Shutdown section under Applications Information for more details. EN can be connected to IN if not used.
NR	4	Fixed voltage versions only—connecting an external capacitor to this pin bypasses noise generated by the internal bandgap, reducing output noise to very low levels.
FB	4	Adjustable voltage version only—this is the input to the control loop error amplifier, and is used to set the output voltage of the device.
OUT	5	Output of the Regulator. There are no output capacitor requirements for stability.



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TYPICAL CHARACTERISTICS

For all voltage versions at $T_J = 25$ °C, $V_{IN} = 2.4$ V, $I_{OUT} = 10$ mA, $V_{EN} = 1.7$ V, and $C_{OUT} = 0.1$ µF, unless otherwise noted.

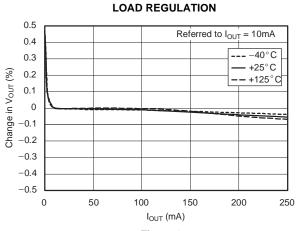


Figure 3.

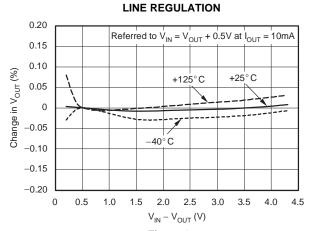


Figure 4.

DROPOUT VOLTAGE vs OUTPUT CURRENT

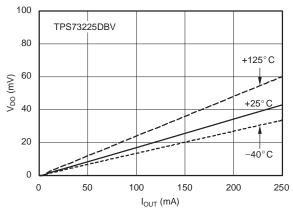


Figure 5.

DROPOUT VOLTAGE vs TEMPERATURE

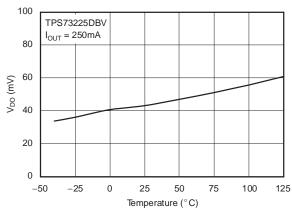


Figure 6.

OUTPUT VOLTAGE ACCURACY HISTOGRAM

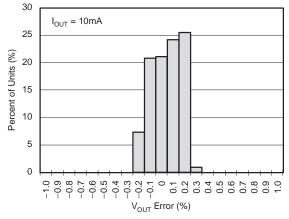


Figure 7.

OUTPUT VOLTAGE DRIFT HISTOGRAM

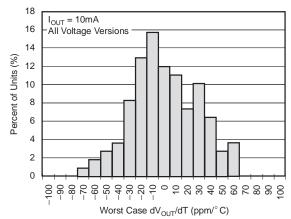


Figure 8.

TYPICAL CHARACTERISTICS (continued)

For all voltage versions at $T_J = 25^{\circ}C$, $V_{IN} = 2.4V$, $I_{OUT} = 10mA$, $V_{EN} = 1.7V$, and $C_{OUT} = 0.1 \mu F$, unless otherwise noted.

GROUND PIN CURRENT vs OUTPUT CURRENT

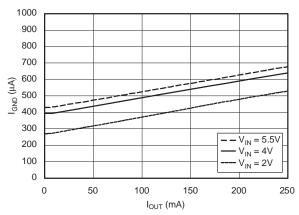


Figure 9.

GROUND PIN CURRENT vs TEMPERATURE

ISTRUMENTS

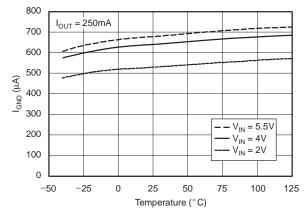


Figure 10.

GROUND PIN CURRENT IN SHUTDOWN vs TEMPERATURE

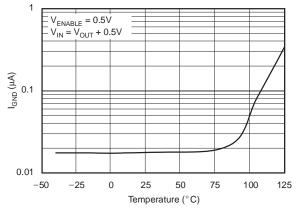


Figure 11.

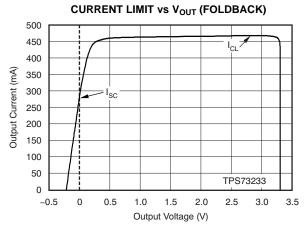


Figure 12.

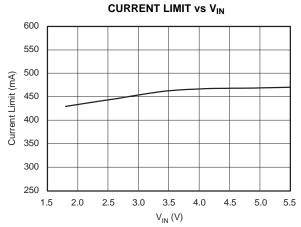


Figure 13.

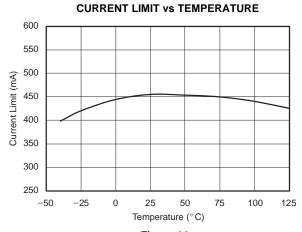


Figure 14.



TYPICAL CHARACTERISTICS (continued)

For all voltage versions at $T_J = 25$ °C, $V_{IN} = 2.4$ V, $I_{OUT} = 10$ mA, $V_{EN} = 1.7$ V, and $C_{OUT} = 0.1 \mu$ F, unless otherwise noted.

PSRR (RIPPLE REJECTION) vs FREQUENCY

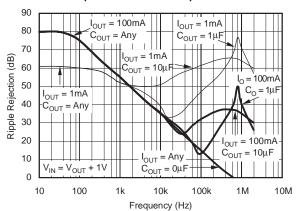


Figure 15.

40 35 30 25 8 20 20 20 5 15 10 Frequency = 10kHz C_{OUT} = 10µF 5 - V_{OUT} = 2.5V I_{OUT} = 100mA

PSRR (RIPPLE REJECTION) vs V_{IN} - V_{OUT}

V_{IN} - V_{OUT} (V) **Figure 16.**

8.0

1.0 1.2

1.4 1.6

1.8 2.0

0.2 0.4 0.6

NOISE SPECTRAL DENSITY $C_{NR} = 0 \mu F \label{eq:cnr}$

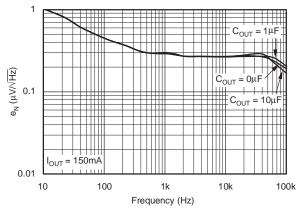


Figure 17.

NOISE SPECTRAL DENSITY $C_{NR} = 0.01 \mu F \label{eq:cnr}$

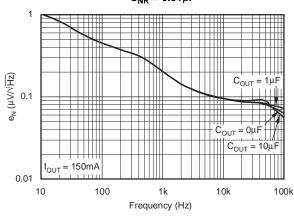


Figure 18.

RMS NOISE VOLTAGE vs Cout

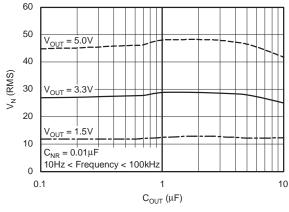


Figure 19.

RMS NOISE VOLTAGE vs C_{NR}

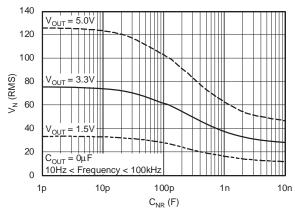


Figure 20.

TEXAS INSTRUMENTS

TYPICAL CHARACTERISTICS (continued)

For all voltage versions at $T_J = 25^{\circ}C$, $V_{IN} = 2.4V$, $I_{OUT} = 10mA$, $V_{EN} = 1.7V$, and $C_{OUT} = 0.1 \mu F$, unless otherwise noted.

TPS73233 LOAD TRANSIENT RESPONSE

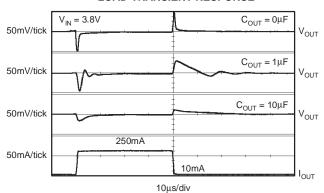


Figure 21.

TPS73233 LINE TRANSIENT RESPONSE

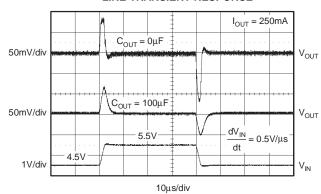


Figure 22.

TPS73233 TURN-ON RESPONSE

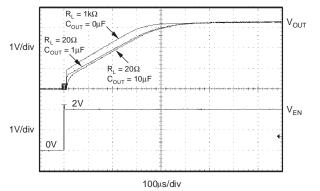


Figure 23.

TPS73233 TURN-OFF RESPONSE

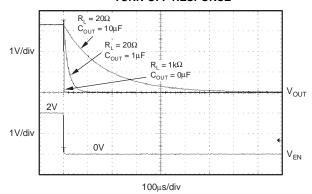


Figure 24.

TPS73233 POWER UP / POWER DOWN

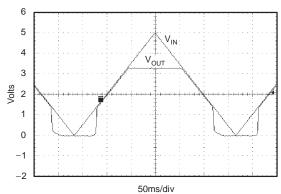


Figure 25.



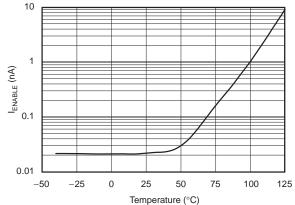


Figure 26.



TYPICAL CHARACTERISTICS (continued)

For all voltage versions at $T_J = 25^{\circ}C$, $V_{IN} = 2.4V$, $I_{OUT} = 10mA$, $V_{EN} = 1.7V$, and $C_{OUT} = 0.1 \mu F$, unless otherwise noted.

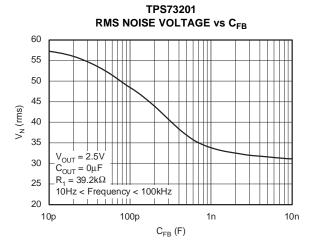


Figure 27.

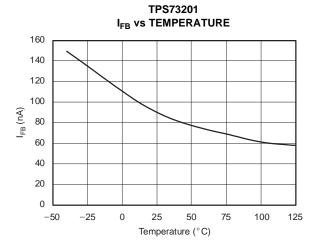


Figure 28.

TPS73201 LOAD TRANSIENT, ADJUSTABLE VERSION

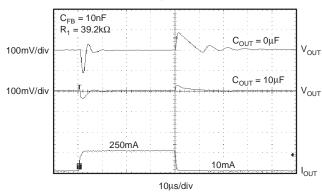


Figure 29.

TPS73201 LINE TRANSIENT, ADJUSTABLE VERSION

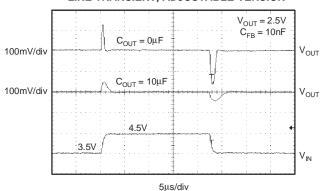


Figure 30.



APPLICATION INFORMATION

The TPS73219 belongs to a family of new generation LDO regulators that use an NMOS pass transistor to achieve ultra-low-dropout performance, reverse current blockage, and freedom from output capacitor constraints. These features, combined with low noise and an enable input, make the TPS73219 ideal for portable applications. This regulator family offers a wide selection of fixed output voltage versions and an adjustable output version. All versions have thermal and over-current protection, including foldback current limit.

Figure 31 shows the basic circuit connections for the fixed voltage models.

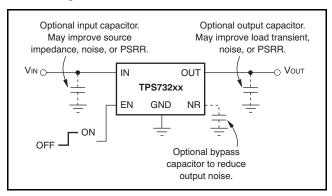


Figure 31. Typical Application Circuit for Fixed-Voltage Versions

For best accuracy, make the parallel combination of R_1 and R_2 approximately equal to $19k\Omega.$ This $19k\Omega,$ in addition to the internal $8k\Omega$ resistor, presents the same impedance to the error amp as the $27k\Omega$ bandgap reference output. This impedance helps compensate for leakages into the error amp terminals.

INPUT AND OUTPUT CAPACITOR REQUIREMENTS

Although an input capacitor is not required for stability, it is good analog design practice to connect a 0.1 μF to 1 μF low ESR capacitor across the input supply near the regulator. This counteracts reactive input sources and improves transient response, noise rejection, and ripple rejection. A higher-value capacitor may be necessary if large, fast rise-time load transients are anticipated or the device is located several inches from the power source.

The TPS73219 does not require an output capacitor for stability and has maximum phase margin with no capacitor. It is designed to be stable for all available

types and values of capacitors. In applications where multiple low ESR capacitors are in parallel, ringing may occur when the product of C_{OUT} and total ESR drops below $50n\Omega F$. Total ESR includes all parasitic resistances, including capacitor ESR and board, socket, and solder joint resistance. In most applications, the sum of capacitor ESR and trace resistance will meet this requirement.

OUTPUT NOISE

A precision band-gap reference is used to generate the internal reference voltage, $V_{REF}.$ This reference is the dominant noise source within the TPS73219 and it generates approximately $32\mu V_{RMS}$ (10Hz to 100kHz) at the reference output (NR). The regulator control loop gains up the reference noise with the same gain as the reference voltage, so that the noise voltage of the regulator is approximately given by:

$$V_N = 32 \mu V_{RMS} \times \frac{(R_1 + R_2)}{R_2} = 32 \mu V_{RMS} \times \frac{V_{OUT}}{V_{REF}}$$
 (1)

Since the value of V_{REF} is 1.2V, this relationship reduces to:

$$V_{N}(\mu V_{RMS}) = 27 \left(\frac{\mu V_{RMS}}{V}\right) \times V_{OUT}(V)$$
 (2)

for the case of no C_{NR} .

An internal $27k\Omega$ resistor in series with the noise reduction pin (NR) forms a low-pass filter for the voltage reference when an external noise reduction capacitor, C_{NR} , is connected from NR to ground. For $C_{NR}=10n\text{F}$, the total noise in the 10Hz to 100kHz bandwidth is reduced by a factor of ~3.2, giving the approximate relationship:

$$V_{N}(\mu V_{RMS}) = 8.5 \left(\frac{\mu V_{RMS}}{V}\right) \times V_{OUT}(V)$$
 (3)

for $C_{NR} = 10nF$.

This noise reduction effect is shown as *RMS Noise Voltage vs* C_{NR} (Figure 20) in the Typical Characteristics section.

The TPS73219 uses an internal charge pump to develop an internal supply voltage sufficient to drive the gate of the NMOS pass element above $V_{\text{OUT}}.$ The charge pump generates ~250µV of switching noise at ~4MHz; however, charge-pump noise contribution is negligible at the output of the regulator for most values of I_{OUT} and $C_{\text{OUT}}.$



BOARD LAYOUT RECOMMENDATION TO IMPROVE PSRR AND NOISE PERFORMANCE

To improve ac performance such as PSRR, output noise, and transient response, it is recommended that the PCB be designed with separate ground planes for V_{IN} and V_{OUT} , with each ground plane connected only at the GND pin of the device. In addition, the ground connection for the bypass capacitor should connect directly to the GND pin of the device.

INTERNAL CURRENT LIMIT

The TPS73219 internal current limit helps protect the regulator during fault conditions. Foldback current limit helps to protect the regulator from damage during output short-circuit conditions by reducing current limit when $V_{\rm OUT}$ drops below 0.5V. See Figure 12 in the Typical Characteristics section for a graph of $I_{\rm OUT}$ vs $V_{\rm OUT}$.

Note from Figure 12 that approximately -0.2V of V_{OUT} results in a current limit of 0mA. Therefore, if OUT is forced below -0.2V before EN goes high, the device may not start up. In applications that work with both a positive and negative voltage supply, the TPS73219 should be enabled first.

ENABLE PIN AND SHUTDOWN

The enable pin (EN) is active high and is compatible with standard TTL-CMOS levels. A V_{EN} below 0.5V (max) turns the regulator off and drops the GND pin current to approximately 10nA. When EN is used to shutdown the regulator, all charge is removed from the pass transistor gate, and the output ramps back up to a regulated V_{OUT} (see Figure 23).

When shutdown capability is not required, EN can be connected to V_{IN} . However, the pass gate may not be discharged using this configuration, and the pass transistor may be left on (enhanced) for a significant

time after $V_{\rm IN}$ has been removed. This scenario can result in reverse current flow (if the IN pin is low impedance) and faster ramp times upon power-up. In addition, for $V_{\rm IN}$ ramp times slower than a few milliseconds, the output may overshoot upon power-up.

Note that current limit foldback can prevent device start-up under some conditions. See the *Internal Current Limit* section.

DROPOUT VOLTAGE

The TPS73219 uses an NMOS pass transistor to achieve extremely low dropout. When $(V_{IN} - V_{OUT})$ is less than the dropout voltage (V_{DO}) , the NMOS pass device is in its linear region of operation and the input-to-output resistance is the R_{DS-ON} of the NMOS pass element.

For large step changes in load current, the TPS73219 requires a larger voltage drop from V_{IN} to V_{OUT} to avoid degraded transient response. The boundary of this transient dropout region is approximately twice the dc dropout. Values of $V_{\text{IN}} - V_{\text{OUT}}$ above this line insure normal transient response.

Operating in the transient dropout region can cause an increase in recovery time. The time required to recover from a load transient is a function of the magnitude of the change in load current rate, the rate of change in load current, and the available headroom (V_{IN} to V_{OUT} voltage drop). Under worst-case conditions [full-scale instantaneous load change with ($V_{\text{IN}} - V_{\text{OUT}}$) close to dc dropout levels], the TPS73219 can take a couple of hundred microseconds to return to the specified regulation accuracy.



TRANSIENT RESPONSE

The low open-loop output impedance provided by the NMOS pass element in a voltage follower configuration allows operation without an output capacitor for many applications. As with any regulator, the addition of a capacitor (nominal value $1\mu F)$ from the OUT pin to ground will reduce undershoot magnitude but increase its duration. In the adjustable version, the addition of a capacitor, C_{FB} , from the OUT pin to the FB pin will also improve the transient response.

The TPS73219 does not have active pull-down when the output is over-voltage. This allows applications that connect higher voltage sources, such as alternate power supplies, to the output. This also results in an output overshoot of several percent if the load current quickly drops to zero when a capacitor is connected to the output. The duration of overshoot can be reduced by adding a load resistor. The overshoot decays at a rate determined by output capacitor C_{OUT} and the internal/external load resistance. The rate of decay is given by:

(Fixed voltage version)

$$dV/dt = \frac{V_{OUT}}{C_{OUT} \times 80k\Omega \parallel R_{LOAD}}$$
 (4)

REVERSE CURRENT

The NMOS pass element of the TPS73219 provides inherent protection against current flow from the output of the regulator to the input when the gate of the pass device is pulled low. To ensure that all charge is removed from the gate of the pass element, the EN pin must be driven low before the input voltage is removed. If this is not done, the pass element may be left on due to stored charge on the gate.

After the EN pin is driven low, no bias voltage is needed on any pin for reverse current blocking. Note that reverse current is specified as the current flowing out of the IN pin due to voltage applied on the OUT pin. There will be additional current flowing into the OUT pin due to the $80k\Omega$ internal resistor divider to ground (see Figure 2).

THERMAL PROTECTION

Thermal protection disables the output when the junction temperature rises to approximately +160°C, allowing the device to cool. When the junction temperature cools to approximately +140°C, the output circuitry is again enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This limits the dissipation of the regulator, protecting it from damage due to overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heatsink. For reliable operation, junction temperature should be limited to +125°C maximum. To estimate the margin of safety in a complete design (including heatsink), increase the temperature until the thermal protection is triggered; use worst-case loads and signal conditions. For good reliability, thermal protection should trigger at least +35°C above the maximum expected ambient condition of your application. This produces a worst-case junction temperature of +125°C at the expected ambient temperature highest worst-case load.

The internal protection circuitry of the TPS73219 has been designed to protect against overload conditions. It was not intended to replace proper heatsinking. Continuously running the TPS73219 into thermal shutdown will degrade device reliability.

POWER DISSIPATION

The ability to remove heat from the die is different for each package type, presenting different considerations in the PCB layout. The PCB area around the device that is free of other components moves the heat from the device to the ambient air. Performance data for JEDEC low- and high-K boards are shown in the Thermal Information table. Using heavier copper will increase the effectiveness in removing heat from the device. The addition of plated through-holes to heat-dissipating layers will also improve the heat-sink effectiveness.

Power dissipation depends on input voltage and load conditions. Power dissipation (P_D) is equal to the product of the output current times the voltage drop across the output pass element (V_{IN} to V_{OUT}):

$$P_{D} = (V_{IN} - V_{OUT}) \times I_{OUT}$$
(5)

Power dissipation can be minimized by using the lowest possible input voltage necessary to assure the required output voltage.

PACKAGE MOUNTING

Solder pad footprint recommendations for the TPS73219 are presented in Application Bulletin Solder Pad Recommendations for Surface-Mount Devices (SBFA015), available from the Texas Instruments web site at www.ti.com.





11-Apr-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
TPS73219DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	CGE	Samples
TPS73219DBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	CGE	Samples
TPS73219DBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	CGE	Samples
TPS73219DBVTG4	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	CGE	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

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⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.



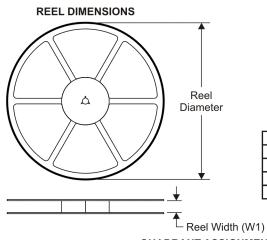


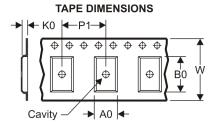
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PACKAGE MATERIALS INFORMATION

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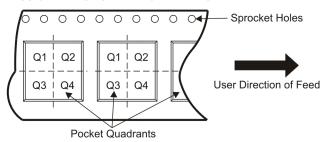
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS73219DBVR	SOT-23	DBV	5	3000	(mm) 178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TPS73219DBVT	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3

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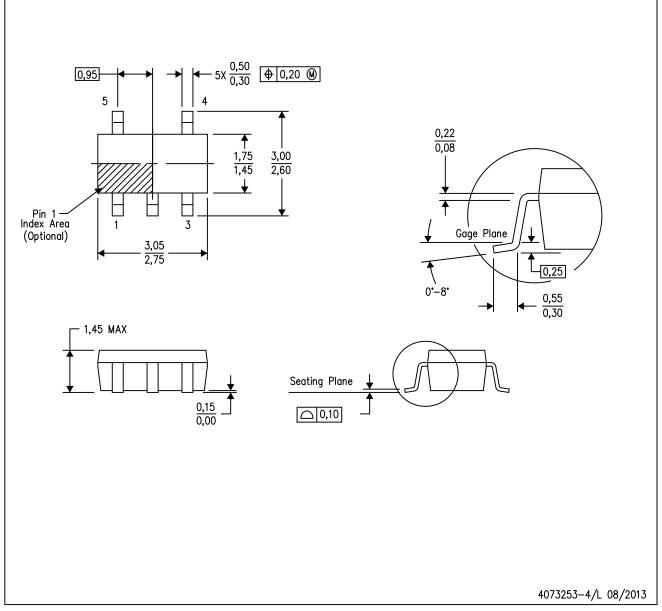


*All dimensions are nominal

Device	Package Type Package Drav		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS73219DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TPS73219DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



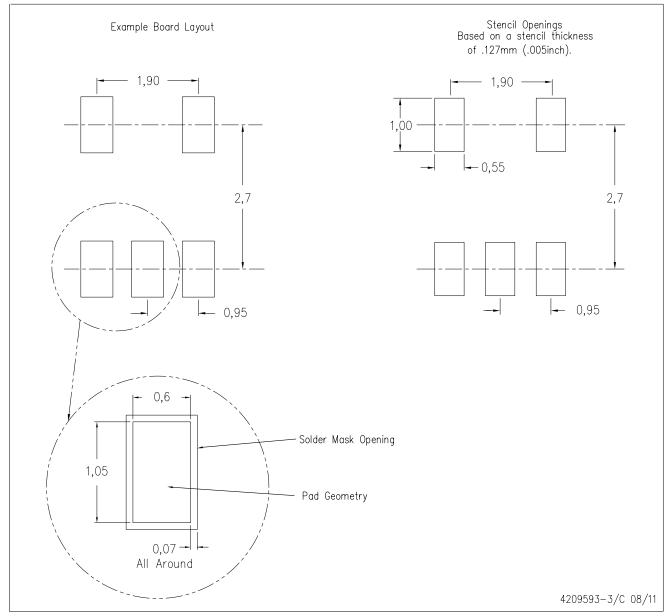
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-178 Variation AA.



DBV (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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